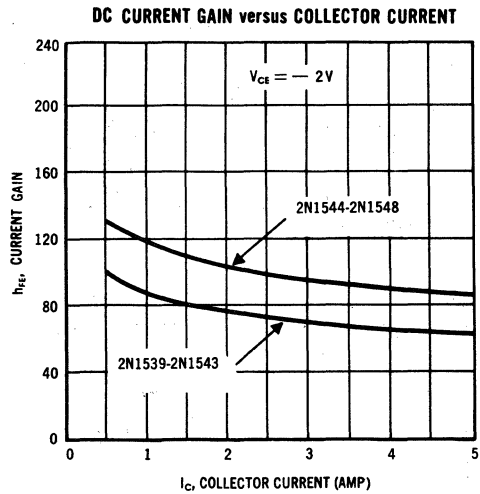
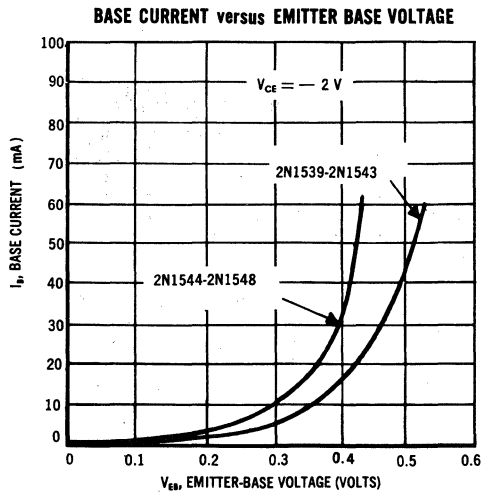
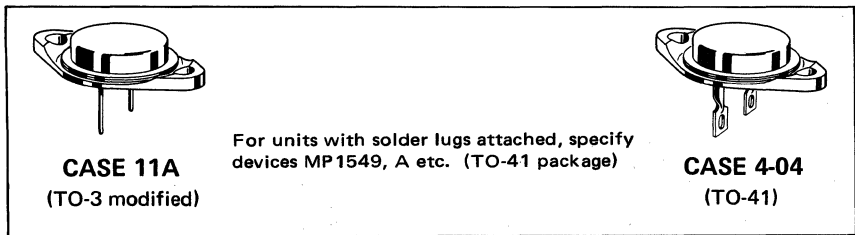


2N1539 thru 2N1548 (continued)



2N1549, A thru 2N1560, A (GERMANIUM)

PNP germanium power transistors for switching and amplifier applications in high-reliability equipment.



MAXIMUM RATINGS Apply to corresponding "Hi-Rel" Series also

Rating	Symbol	2N1549 2N1553 2N1557	2N1550 2N1554 2N1558	2N1551 2N1555 2N1559	2N1552 2N1556 2N1560	Units
Collector-Emitter Voltage	V_{CEX}	40	60	80	100	Vdc
Collector-Emitter Voltage	V_{CES}^*	30	45	60	75	Vdc
Collector-Emitter Voltage	V_{CEO}^*	20	30	40	50	Vdc
Collector-Base Voltage	V_{CB}	40	60	80	100	Vdc
Emitter-Base Voltage	V_{EB}	20	30	40	50	Vdc
Collector Current (Continuous)	I_C	15				Amp
Collector Current (Peak)	I_C	20				Amp
Collector Junction Temperature	T_J	-65 to +110				$^{\circ}C$
Collector Dissipation (25 $^{\circ}C$ Case Temp.)	P_D	106				Watts
Thermal Resistance	θ_{JC}	0.8				$^{\circ}C/W$

*To avoid excessive heating of collector junction, perform this test with a sweep method.

2N1549 thru 2N1560 (continued)

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristics apply to corresponding A type numbers also.

Characteristic	Symbol	Min	Max	Unit
Collector-Base Cutoff Current ($V_{CB} = 25\text{ V}$) 2N1549, 2N1553, 2N1557 ($V_{CB} = 40\text{ V}$) 2N1550, 2N1554, 2N1558 ($V_{CB} = 55\text{ V}$) 2N1551, 2N1555, 2N1559 ($V_{CB} = 65\text{ V}$) 2N1552, 2N1556, 2N1560	I_{CBO1}	-	3.0	mA
Collector-Base Cutoff Current ($V_{CB} = 2\text{ V}$) ($V_{CB} = 1/2\text{ BV}_{CES}$ rating; $T_C = +90^\circ\text{C}$)	I_{CBO}	-	0.2 20	mA
Emitter-Base Cutoff Current ($V_{EB} = 12\text{ V}$)	I_{EBO}	-	0.5	mA
Collector-Emitter Breakdown Voltage ($I_C = 300\text{ mA}$) 2N1549, 2N1553, 2N1557 2N1550, 2N1554, 2N1558 2N1551, 2N1555, 2N1559 2N1552, 2N1556, 2N1560	BV_{CES}	30 45 60 75	- - - -	volts
Collector-Emitter Leakage Current ($V_{BE} = 1.0\text{ V}$, V_{CE} @ rated BV_{CBO})	I_{CEX}	-	20	mA
Collector-Emitter Breakdown Voltage* ($I_C = 300\text{ mA}$, $I_B = 0$) 2N1549, 2N1553, 2N1557 2N1550, 2N1554, 2N1558 2N1551, 2N1555, 2N1559 2N1552, 2N1556, 2N1560	BV_{CEO}^*	20 30 40 50	- - - -	volts
Collector-Base Breakdown Voltage ($I_C = 20\text{ mA}$) 2N1549, 2N1553, 2N1557 2N1550, 2N1554, 2N1558 2N1551, 2N1555, 2N1559 2N1552, 2N1556, 2N1560	BV_{CBO}	40 60 80 100	- - - -	volts
Current Gain ($V_{CE} = 2.0\text{ V}$, $I_C = 10\text{ A}$) 2N1549 - 2N1552 2N1553 - 2N1556 2N1557 - 2N1560	h_{FE1}	10 30 50	30 60 100	-
Base-Emitter Drive Voltage ($I_C = 10\text{ A}$, $I_B = 1.0\text{ A}$) 2N1549 - 2N1552 2N1553 - 2N1556 2N1557 - 2N1560	V_{BE}	- - -	1.3 1.0 0.85	volts
Collector Saturation Voltage ($I_C = 10\text{ A}$, $I_B = 1.0\text{ A}$) 2N1549 - 2N1552 2N1553 - 2N1556 2N1557 - 2N1560	$V_{CE(sat)}$	- - -	1.0 0.7 0.5	volts

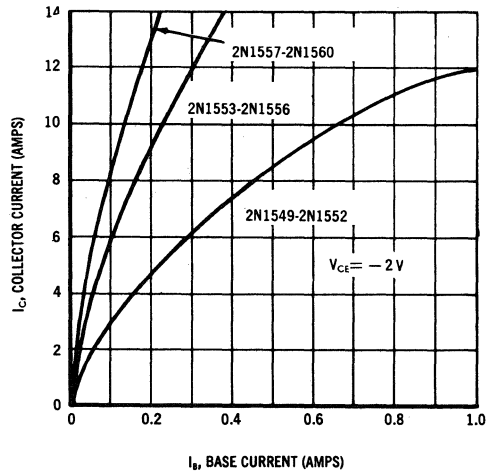
*To avoid excessive heating of collector junction, perform this test with a sweep method.

2N1549 thru 2N1560 (continued)

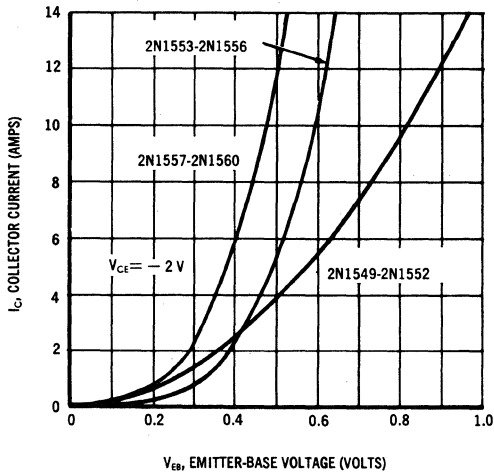
ELECTRICAL CHARACTERISTICS (continued)

Characteristic	Symbol	Min	Max	Unit
Transconductance (V _{CE} = 2.0 V, I _C = 10 A)	g _{FE}			mhos
2N1549 - 2N1552		6.0	18	
2N1553 - 2N1556		8.0	30	
2N1557 - 2N1560		12	40	
Frequency Cutoff	f _{ae}	Typ		kHz
2N1549 - 2N1552		10		
2N1553 - 2N1556		6.0		
2N1557 - 2N1560		5.0		

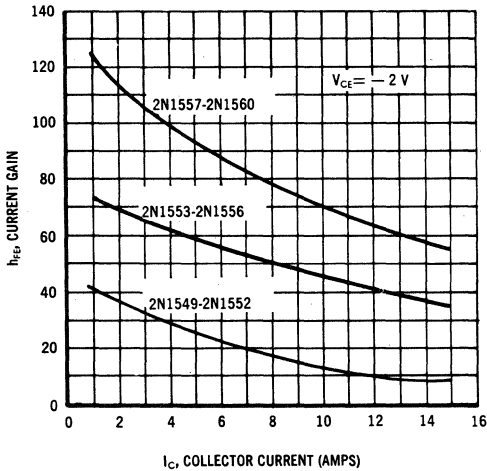
COLLECTOR CURRENT versus BASE CURRENT



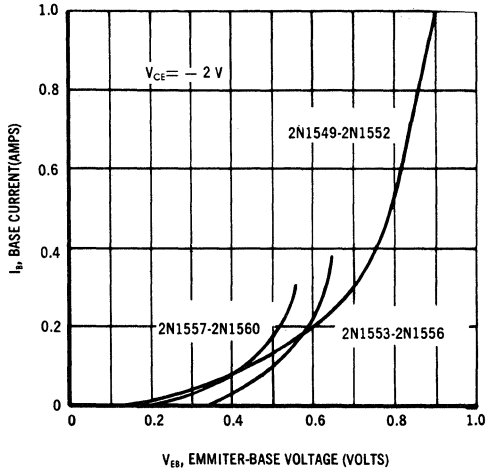
COLLECTOR CURRENT versus EMITTER-BASE VOLTAGE



CURRENT GAIN versus COLLECTOR CURRENT



BASE CURRENT versus EMITTER-BASE VOLTAGE

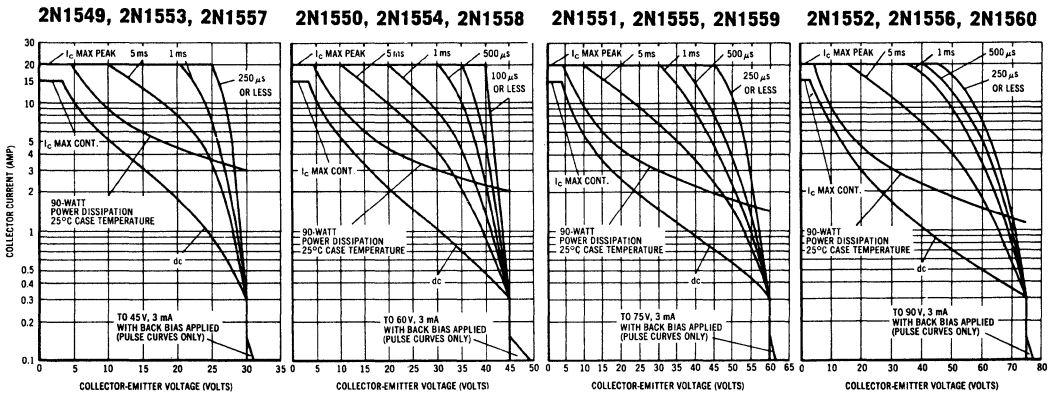


2N1549 thru 2N1560 (continued)

SAFE OPERATING AREAS

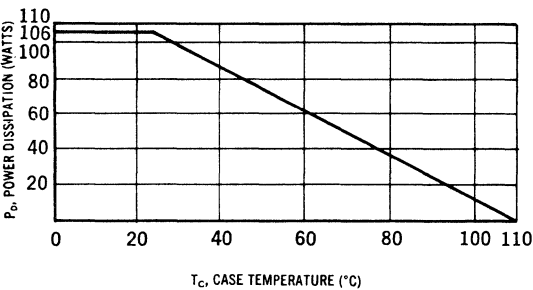
The Safe Operating Area Curves indicate $I_C - V_{CE}$ limits below which the device will not go into secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a collector-emitter short.

(Duty cycle of the excursions make no significant change in these safe areas.) To insure operation below the maximum T_J , the power-temperature derating curve must be observed for both steady state and pulse power conditions.

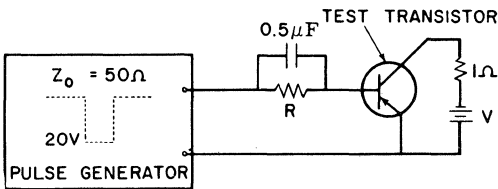


POWER-TEMPERATURE DERATING CURVE

The maximum continuous power is related to maximum junction temperature, by the thermal resistance factor. For dc or frequencies below 25 Hz the transistor must be operated within the constant $P_D = V_c \times I_c$ hyperbolic curve. This curve has a value of 106 watts at case temperatures of 25°C and is 0 watts at 110°C with a linear relation between the two temperatures such that P_D allowable = $\frac{110^\circ - T_c}{0.8}$



SWITCHING TIME MEASURING UNIT



Devices	Conditions*			Typical Switching Times		
	I_C (Amp)	V (Volts)	R (ohms)	$t_d + t_r$ (µs)	t_f (µs)	t_r (µs)
2N1549 -52	10	10	10	5	2	10
2N1553 -56	10	10	30	10	5	25
2N1557 -60	10	10	50	10	5	25

* Input Pulse Repetition Rate = 2 kHz,
Pulse Width = 50 µs